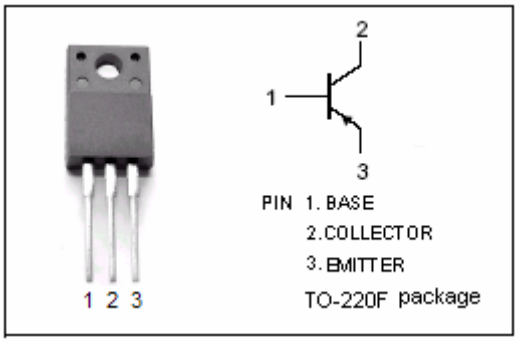
isc Silicon PNP Power Transistor 2SA2140

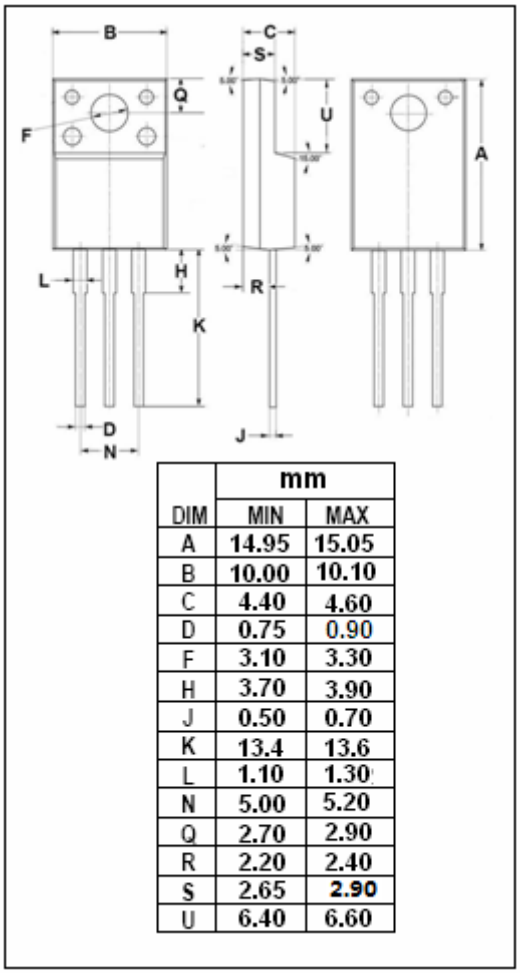


DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= -180V(Min)
- Good Linearity of h_{FE}

APPLICATIONS

- Designed for power amplification and for TV VM circuit.



DIM	mm MIN	mm MAX
A	14.95	15.05
B	10.00	10.10
C	4.40	4.60
D	0.75	0.90
F	3.10	3.30
H	3.70	3.90
J	0.50	0.70
K	13.4	13.6
L	1.10	1.30
N	5.00	5.20
Q	2.70	2.90
R	2.20	2.40
S	2.65	2.90
U	6.40	6.60

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-180	V
V_{CEO}	Collector-Emitter Voltage	-180	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-1.5	A
I_{CP}	Collector Current-Peak	-3	A
P_C	Collector Power Dissipation @T_a=25℃	2	W
	Collector Power Dissipation @T_C=25℃	20	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃

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ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -10mA ; I_B= 0	-180			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -1A; I_B= -0.1A			-0.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -180V ; I_E= 0			-100	μ A
I_{EBO}	Emitter Cutoff Current	V_{EB}= -6V; I_C= 0			-100	μ A
h_{FE}	DC Current Gain	I_C= -0.1A ; V_{CE}= -5V	60		240	
C_{OB}	Collector Output Capacitance	I_E= 0; V_{CB}= -10V; f= 1MHz		30		pF
f_T	Current-Gain—Bandwidth Product	I_C= -0.2A; V_{CE}= -10V; f= 10MHz		100		MHz
Switching Times						
t_{on}	Turn-on Time	I_C= -0.4A,V_{CC}= 100V I_{B1}= -I_{B2}= -0.04A		0.1		μ s
t_{stg}	Storage Time			1.0		μ s
t_f	Fall Time			0.1		μ s

◆ h_{FE} Classifications

Q	P
60-140	120-240